

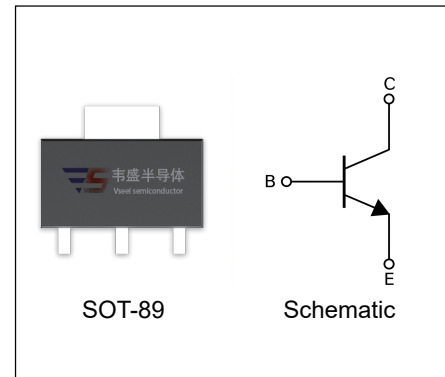
2SC2881 TRANSISTOR (NPN)

FEATURES

- Small Flat Package
- High Transition Frequency
- High Voltage
- Complementary to 2SA1201

APPLICATIONS

- Power Amplifier and Voltage Amplifier



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

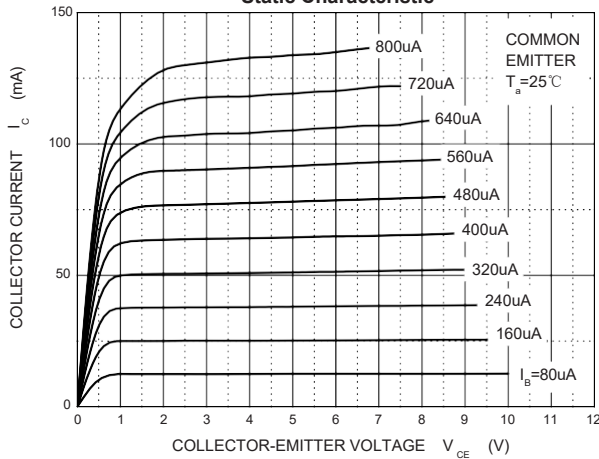
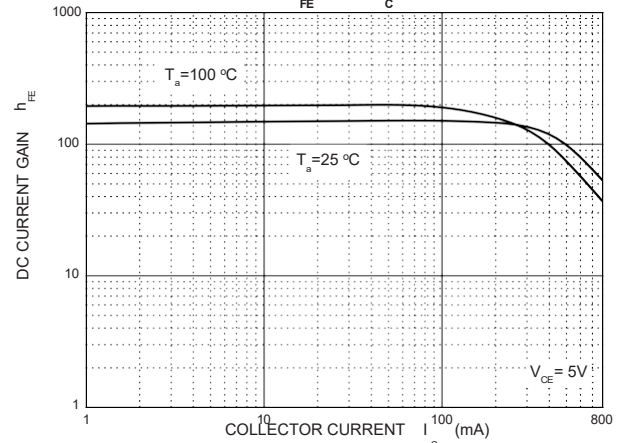
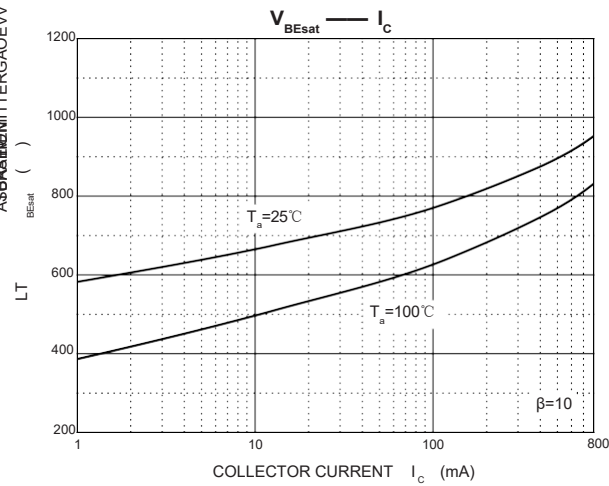
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	800	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=120V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=100mA$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1	V
Base-emitter voltage	V_{BE}	$V_{CE}=5V, I_C=0.5A$			1	V
Transition frequency	f_T	$V_{CE}=5V, I_C=100mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			30	pF

CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	80 - 160	120 - 240

Static Characteristic

 $h_{FE} - I_C$

 $V_{BEsat} - I_C$

 $V_{CEsat} - I_C$
